

MJE15034 NPN, MJE15035 PNP

Preferred Device

Complementary Silicon Plastic Power Transistors

TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high-frequency drivers in audio amplifiers.

Features

- $h_{FE} = 100$ (Min) @ $I_C = 0.5$ Adc
= 10 (Min) @ $I_C = 2.0$ Adc
- Collector-Emitter Sustaining Voltage –
 $V_{CEO(sus)} = 350$ Vdc (Min) – MJE15034, MJE15035
- High Current Gain – Bandwidth Product
 $f_T = 30$ MHz (Min) @ $I_C = 500$ mA
- TO-220AB Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Machine Model: C
Human Body Model: 3B
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	350	Vdc
Collector-Base Voltage	V_{CB}	350	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	4.0 8.0	A
Base Current	I_B	1.0	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	50 0.40	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

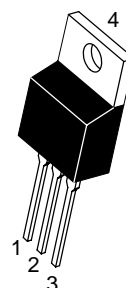
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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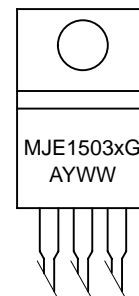
<http://onsemi.com>

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS



TO-220AB
CASE 221A
STYLE 1

MARKING DIAGRAM



MJE1503x = Device Code
x = 4 or 5
A = Location Code
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE15034	TO-220AB	50 Units / Rail
MJE15034G	TO-220AB (Pb-Free)	50 Units / Rail
MJE15035	TO-220AB	50 Units / Rail
MJE15035G	TO-220AB (Pb-Free)	50 Units / Rail

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (Note 1)	(I _C = 10 mA _{dc} , I _B = 0)	V _{CEO(sus)}	350	–	V _{dc}
Collector Cutoff Current	(V _{CB} = 350 V _{dc} , I _E = 0)	I _{CBO}	–	10	μA _{dc}
Emitter Cutoff Current	(V _{BE} = 5.0 V _{dc} , I _C = 0)	I _{EBO}	–	10	μA _{dc}
ON CHARACTERISTICS (Note 1)					
DC Current Gain	(I _C = 0.1 A _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 0.5 A _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 1.0 A _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 2.0 A _{dc} , V _{CE} = 5.0 V _{dc})	h _{FE}	100 100 50 10	– – – –	–
Collector-Emitter Saturation Voltage	(I _C = 1.0 A _{dc} , I _B = 0.1 A _{dc})	V _{CE(sat)}	–	0.5	V _{dc}
Base-Emitter On Voltage	(I _C = 1.0 A _{dc} , V _{CE} = 5.0 V _{dc})	V _{BE(on)}	–	1.0	V _{dc}
DYNAMIC CHARACTERISTICS					
Current Gain – Bandwidth Product (Note 2) (I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc} , f _{test} = 1.0 MHz)		f _T	30	–	MHz

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f_T = |h_{fe}| • f_{test}.

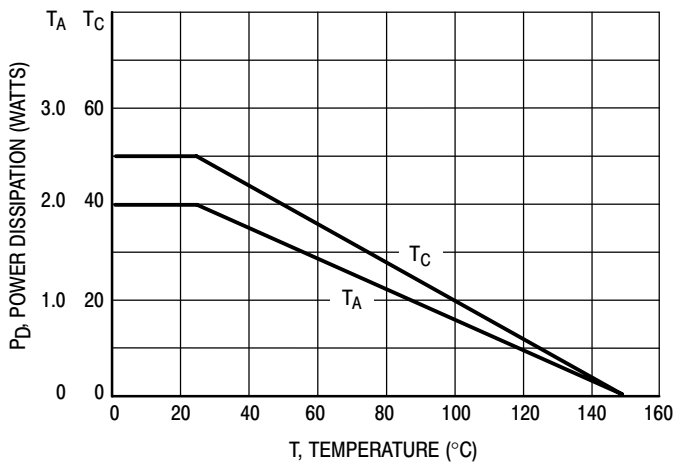


Figure 1. Power Derating

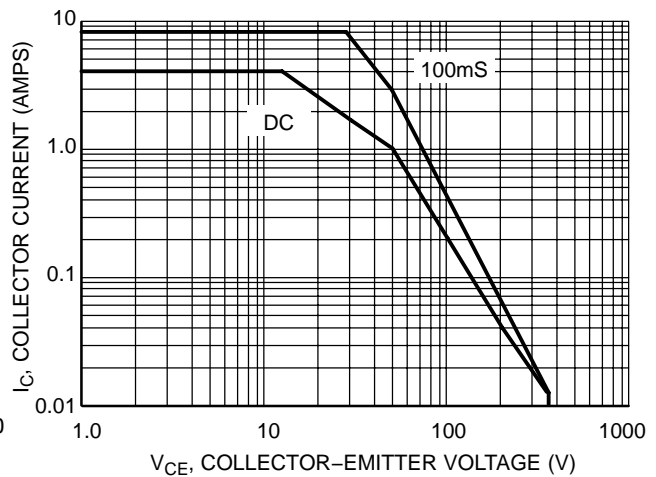


Figure 2. Active Region Safe Operating Area

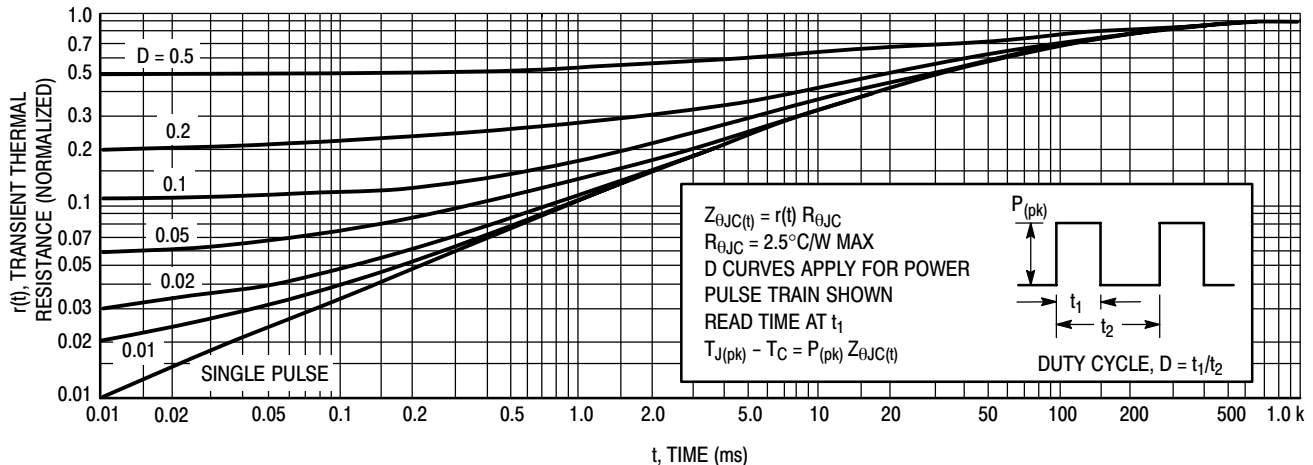
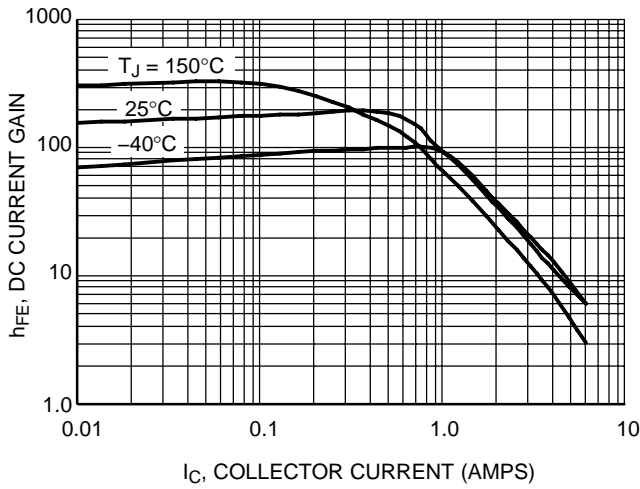
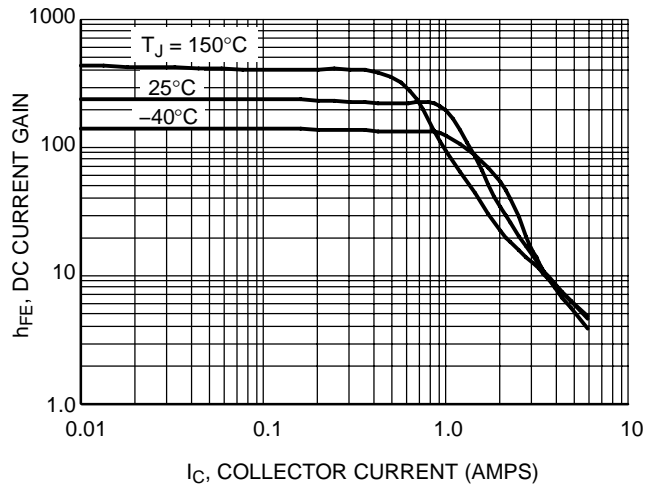


Figure 3. Thermal Response

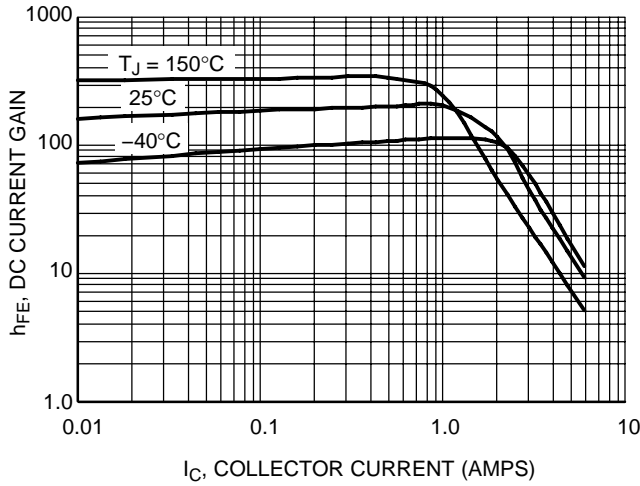
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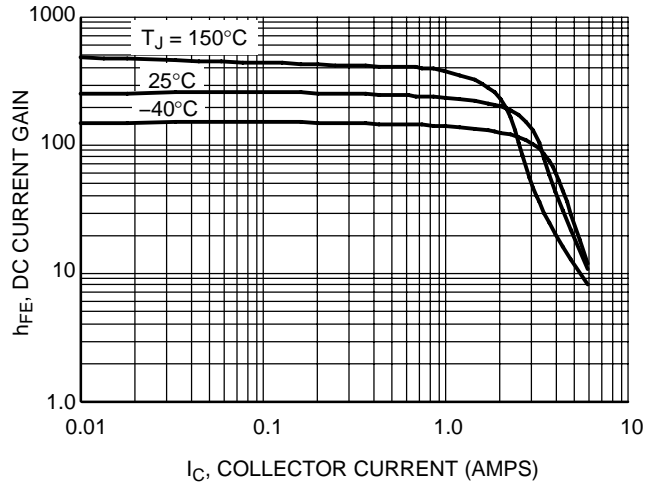
**Figure 4. DC Current Gain, $V_{CE} = 5.0\text{ V}$
NPN MJE15034**



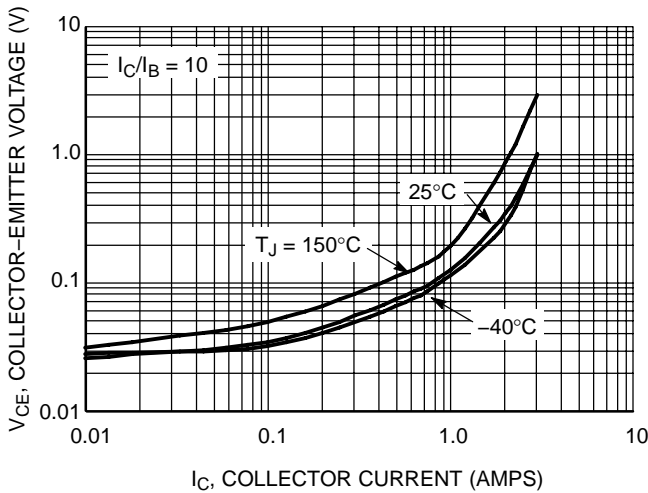
**Figure 5. DC Current Gain, $V_{CE} = 5.0\text{ V}$
PNP MJE15035**



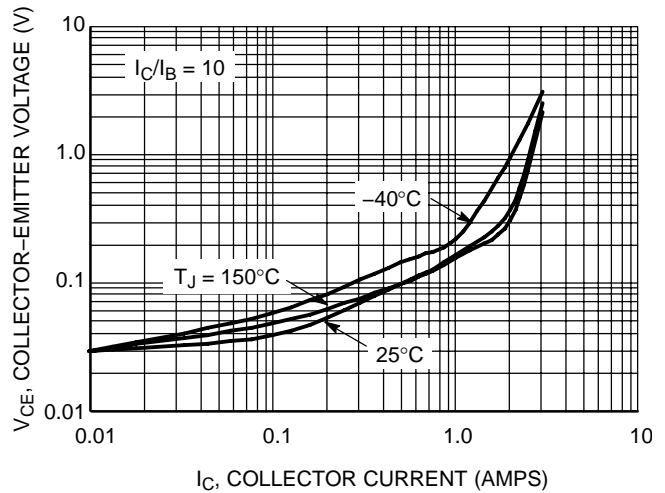
**Figure 6. DC Current Gain, $V_{CE} = 20\text{ V}$
NPN MJE15034**



**Figure 7. DC Current Gain, $V_{CE} = 20\text{ V}$
PNP MJE15035**

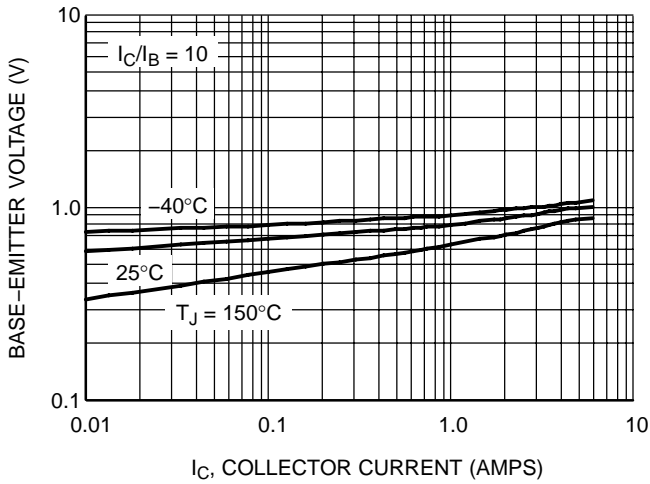


**Figure 8. $V_{CE(sat)}$
NPN MJE15034**

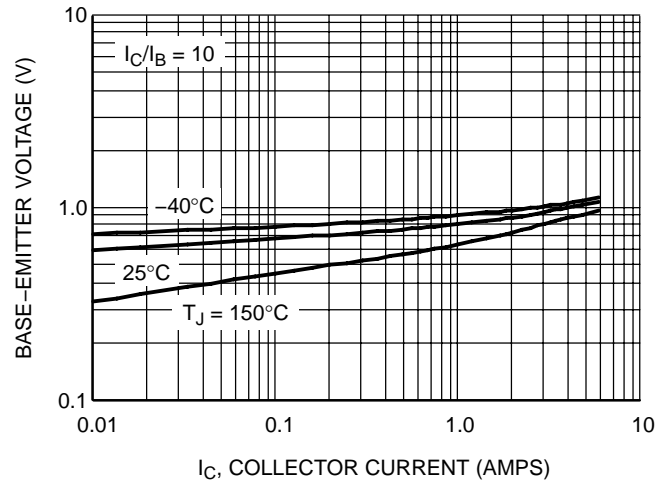


**Figure 9. $V_{CE(sat)}$
PNP MJE15035**

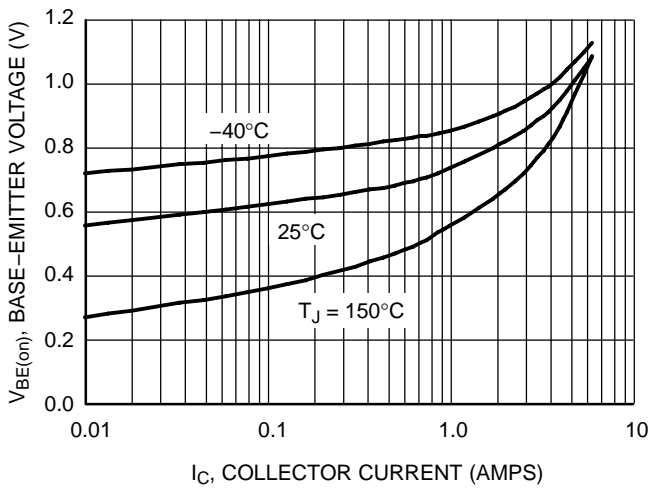
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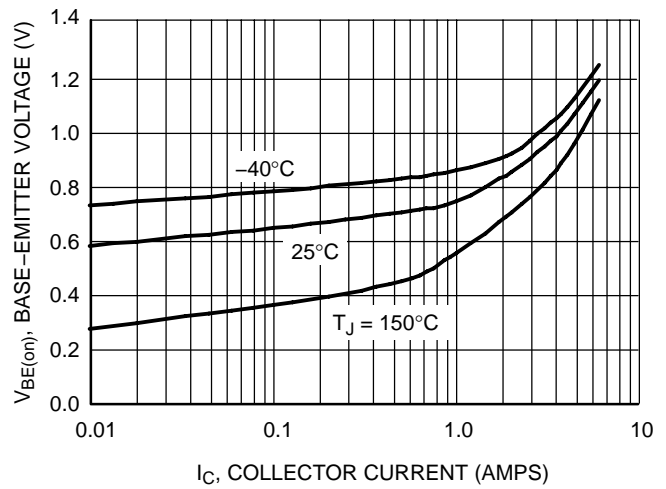
**Figure 10. $V_{BE(sat)}$
NPN MJE15034**



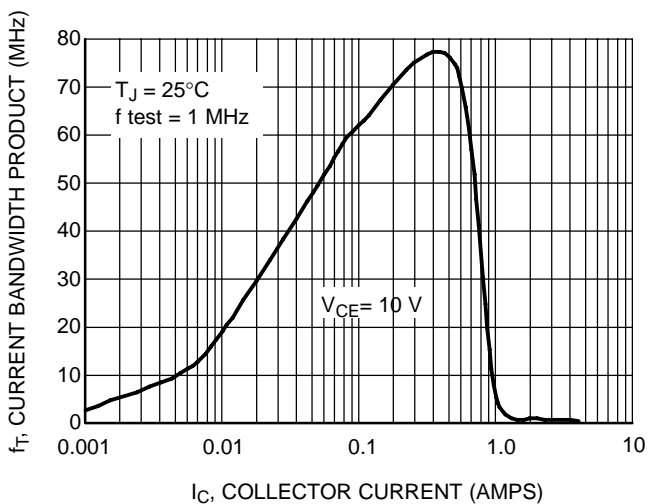
**Figure 11. $V_{BE(sat)}$
PNP MJE15035**



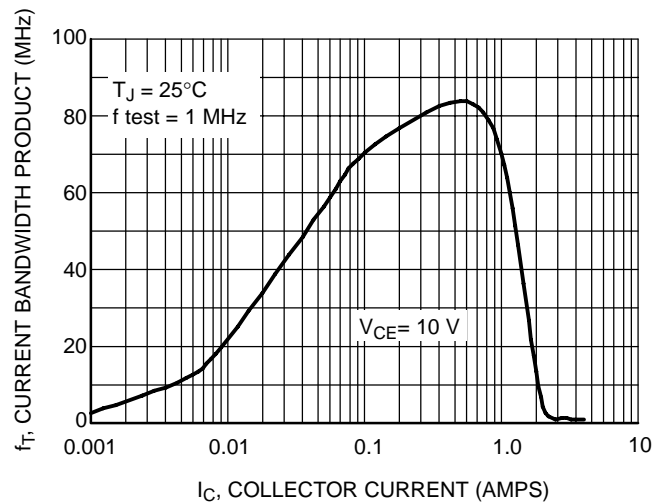
**Figure 12. $V_{BE(on)}$
NPN MJE15034**



**Figure 13. $V_{BE(on)}$
PNP MJE15035**



**Figure 14. Typical Current Gain Bandwidth Product
NPN MJE15034**

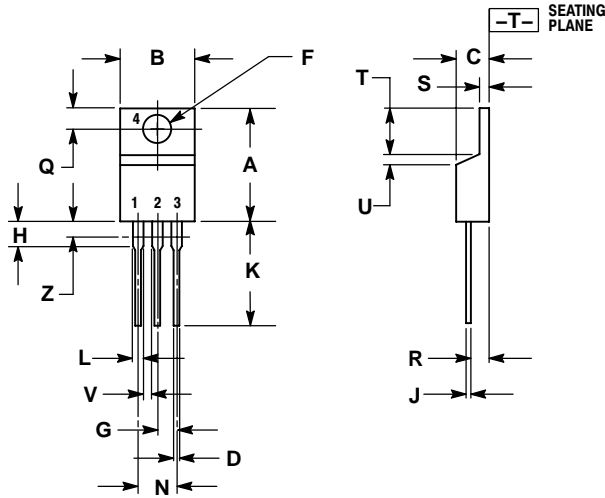


**Figure 15. Typical Current Gain Bandwidth Product
PNP MJE15035**

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PACKAGE DIMENSIONS

TO-220 THREE-LEAD
TO-220AB
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1: BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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